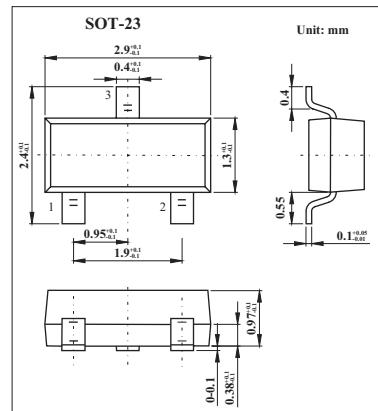


## Schottky Barrier Diodes

### MA3XD14E

#### ■ Features

- Mini type 3-pin package
- Low forward rise voltage  $V_F$  ( $V_F < 0.4$  V)
- Cathode common type



#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	20	V
Repetitive peak reverse-voltage	$I_{RRM}$	20	V
Non-repetitive peak forward-surge-current (Note 2)	$I_{FSM}$	1	A
Forward current (DC)	$I_F$	100	mA
		70	
Peak forward current	$I_{FM}$	300	mA
		200	
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to + 150	$^\circ\text{C}$

Note

1 : The value for operating one chip

2 : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

#### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 10$ V			20	$\mu\text{A}$
Forward voltage (DC)	$V_F$	$I_F = 5$ mA			0.27	V
		$I_F = 100$ mA			0.40	V
Terminal capacitance	$C_t$	$V_R = 0$ V, $f = 1$ MHz		25		pF
Reverse recovery time*	$t_{rr}$	$I_F = I_R = 100$ mA, $I_{rr} = 10$ mA, $R_L = 100 \Omega$		3.0		ns

Note

1. This product is sensitive to electric shock (static electricity, etc.). Due attention must be paid

on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 400 MHz

3. \* :  $t_{rr}$  measuring circuit

#### ■ Marking

Marking	M5H
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